

1. Features and Benefits

- End-of-line programmable sensor
- Ratiometric or fixed (SOIC8 package only) analog output
- Flexible Supply Voltage with factory selectable 5V or 3.3V mode
- Measurement range from ± 12.5 to $\pm 400\text{mT}$
- High speed sensing
 - DC to 400kHz bandwidth
 - $2\mu\text{s}$ response time
- High linearity down to $\pm 0.5\%$ full scale
- Low noise
- AEC-Q100 – Grade 0 Automotive Qualification
- Very low thermal drift for wide temperature range
 - Offset drift ($<5\text{mV}$)
 - Sensitivity drift ($<1\%$)
- Internal and external (SOIC8 package only) overcurrent detection
- RoHS compliant
- Available in SIP4-VA (MSL-1) and SOIC8 packages (MSL-3)



2. Application Examples

- High Voltage Traction Motor Inverter
- 48V Boost Recuperation Inverter
- DCDC Converter
- Smart Battery Junction Boxes
- Smart Fuse Overcurrent Detection

- Redundant monitoring of Battery Management System (BMS)

3. Description

The MLX91219 is a monolithic Hall-effect sensor which is sensitive to the flux density applied orthogonally to the IC surface. The sensor provides an analog output voltage proportional to the applied magnetic flux density.

The transfer characteristic of the MLX91219 is factory trimmed over temperature, and is programmable (offset, sensitivity, filtering, internal overcurrent threshold) during end-of-line customer calibration. With the 400kHz bandwidth and fast response time, it is particularly adapted for high speed applications such as inverters and converters where fast response time due to fast switching is required.

In a typical current sensing application, the sensor is used in combination with a ring shaped soft ferromagnetic core. This core is recommended to be laminated for high bandwidth applications. The MLX91219 is placed in a small air gap and the current conductor – a bus bar or a cable – is passed through the inner part of the ferromagnetic ring. On the one hand the ring concentrates and amplifies the magnetic flux seen by the sensor IC, and at the same time it attenuates external magnetic field disturbances.

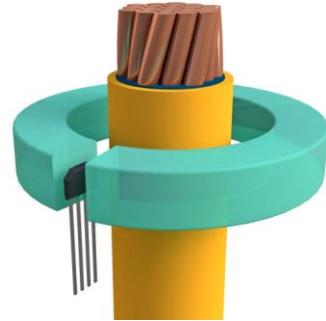


Figure 1. Typical Current Sensing Application for VA package

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4. Ordering Information

Product Code	Temperature	Package	Option Code	Packing Form	Typical Sensitivity	Supply Voltage	Reference Voltage	OCD Level
MLX91219	L	VA	AAA-500	CR	7 mV/mT	5V	NA	134.7 %FS
MLX91219	L	VA	AAA-501	CR	10mV/mT	5V	NA	134.7 %FS
MLX91219	L	DC	ARA-501	RE	10mV/mT	5V	NA	134.7 %FS
MLX91219	L	VA	AAA-502	CR	15mV/mT	5V	NA	134.7 %FS
MLX91219	L	VA	AAA-503	CR	25mV/mT	5V	NA	134.7 %FS
MLX91219	L	DC	ARA-503	RE	25mV/mT	5V	NA	134.7 %FS
MLX91219	L	VA	AAT-511	RE	10mV/mT	5V	NA	88.2 %FS

Table 1: Available ordering codes.

Legend:

Temperature Code	L	from -40°C to 150°C ambient temperature
Package Code	VA	“VA” for SIP-4 VA package
	DC	“DC” for SOIC8 package
Option Code	Axx-xxx	“A” for Silicon revision
	xAx-xxx	“A” for ratiometric output (only for SIP-4 VA package)
	xRx-xxx	“R” for ratiometric output (only for SOIC8 package)
	xFx-xxx	“F” for fixed output (only for SOIC8 package)
	xxA-xxx	VA straight leg (see section 17.3)
	xxR-xxx	Trim and Form type: 90° 2x2x91.3 (h=5.34mm) Bending-STD2 (see section 17.4)
	xxS-xxx	Trim and Form type: 90° 2x2x91.3 (h=3.7mm) Bending-STD3 (see section 17.5)
	xxT-xxx	Trim and Form type: 90° 2x2x91.8 (h=1.68mm) Bending-STD4 (see section 17.6)
	xxZ-xxx	Trim and Form type: SMD style TFT4K1 (see section 17.7)
	xxx-3xx	“3” for 3.3 V supply, bipolar output
	xxx-5xx	“5” for 5 V supply, bipolar output
	xxx-x00	Typical sensitivity of 7 mV/mT and overcurrent detection of 134.7 %full scale
	xxx-x01	Typical sensitivity of 10 mV/mT and overcurrent detection of 134.7 %full scale

Packing Form	CR	Carton Reel – Radial taping
	RE	Plastic Tape on Reel
	SP	Sample pack
Ordering Example	“MLX91219LVA-AAA-500-CR” MLX91219 Conventional Hall current sensor in SIP4-VA package, temperature range -40°C to 150°C. Sensitivity 7 mV/mT. 5V Supply, bipolar ratiometric output. Parts delivered in Carton Reel.	

Table 2: Legend ordering codes.

Melexis is continuously expanding its product portfolio by adding new option codes to better meet the needs of our customer's applications. This table is being updated frequently, please go to the Melexis website to download the latest version of this datasheet. For custom transfer characteristics, please contact your local Melexis Sales representative or distributor.

5. Functional Diagram

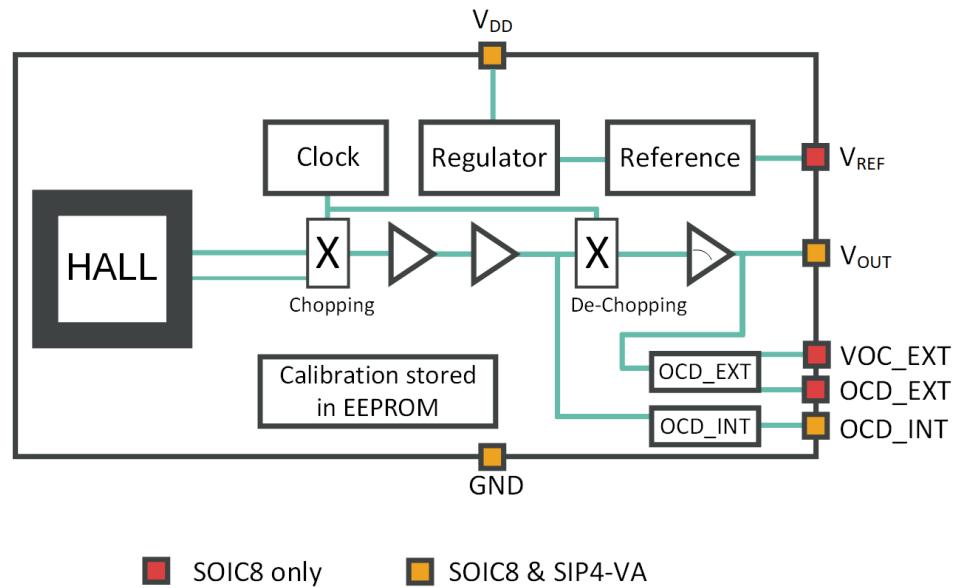


Figure 2: Block Diagram of the MLX91219.

5.1. Ratiometric Mode

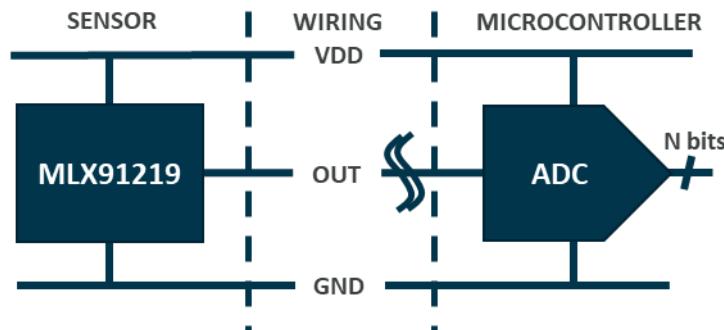


Figure 3: Schematic of ratiometric mode

No matter if the V_{DD} line is at 5V or deviating +/-10%, the ADC code for a given measured magnetic field will always be the same as the ADC is supplied by the same voltage as the sensor.

5.2. Differential or Fixed Mode

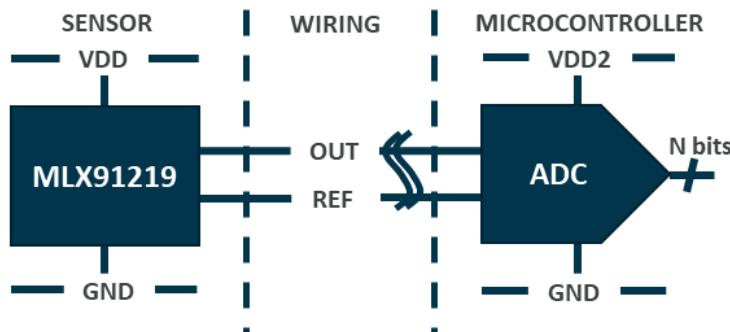


Figure 4: Schematic of fixed mode

In this particular case the ADC does not necessarily share the same supply voltage with the sensor. For this reason, the sensor is calibrated with an absolute sensitivity regardless of the actual supply voltage. The output signal can be reconstructed by taking the difference between the output and the reference voltage from the IC. The ADC gets these two signals as inputs for establishing the sensed magnetic field accurately, and is not influenced by the supply voltage differences between both sensor and microcontroller, if applicable. Only available in SOIC8 package.

Parameter	Ratiometric Mode	Differential or Fixed Mode
Output Signal	$V_{OUT} [\%V_{DD}]$ Example: output is 2.5V when supply is 5V → output is then 50% V_{DD} . If the supply (V_{DD}) increases with 5% to 5.25V the sensor output will (for the same measured input magnetic field) scale proportionally with the supply voltage, becoming 2.625V, but as a percentage (i.e. ratiometrically seen) it remains at 50% of V_{DD} .	$V_{OUT} - V_{REF} [V]$ Example: V_{OUT} and V_{REF} output is 2.501V and V_{REF} is 2.501V when supply is 5V. When the supply voltage is increasing to 5.1V due to supply system variation, the sensor will still maintain the same "fixed" output values V_{OUT} and V_{REF} equal to 2.501V.
Offset (V_{OUT} at magnetic field 0mT)	50 [% V_{DD}] (factory trimmed)	V_{REF} (factory trimmed)
Offset ratiometric	Yes	No
Sensitivity	[% V_{DD}/mT] ¹	[mV/mT]
Sensitivity ratiometric	Yes	No
Measured magnetic field B	$B = \frac{(V_{OUT} - V_{OUT}[0mT])}{Sensitivity}$	$B = \frac{(V_{OUT} - V_{REF})}{Sensitivity}$

Table 3: Parameters of differential and fixed modes

¹ The sensitivity in ratiometric mode is expressed as [% V_{DD}/mT]. However, for simplicity, in the datasheet the sensitivity will be always expressed in [mV/mT]. For ratiometric devices, this corresponds to the sensitivity for $V_{DD}=5V$ or 3.3V, depending on the settings of the sensor.

6. Glossary of Terms

Terms	Definition
TC	Temperature Coefficient
FS	Full Scale, output referred. Corresponds to 2V excursion around 2.5V at 5V supply or 1.25V excursion from 1.65V at 3.3V supply for bipolar designs
T, mT	Tesla, milliTesla = units for the magnetic flux density
G	Gauss = unit for the magnetic flux density [1mT = 10G]
OCD	Overcurrent Detection
MSL	Moisture Sensitivity Level

Table 4: Glossary of Terms

7. Pin Definitions and Descriptions

Note: MLX91219 is not pin-to-pin compatible with MLX91209 or MLX91217.

7.1. SIP-4 VA Package

Pin #	Name	Type	Description
1	VDD	Supply	Supply voltage
2	OUT	Analog Output	Output voltage (measurement)
3	OCD_INT	Analog Output	Overcurrent detection based on internal threshold
4	GND	Supply	Ground voltage

Table 5: Pin definitions and descriptions.

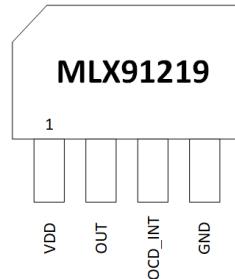


Figure 5: Pinout of SIP4-VA package.

7.2. SOIC8 package

Pin #	Name	Type	Description
1	VREF	Analog	Reference voltage
2	OUT	Analog Output	Output voltage (measurement)
3	GND	Supply	Ground voltage
4	VDD	Supply	Supply voltage
5	NC	-	Not connected
6	OCD_EXT	Analog Output	Overcurrent detection based on external threshold
7	OCD_INT	Analog Output	Overcurrent detection based on internal threshold
8	VOC_EXT	Analog Input	External threshold for the OCD

Table 6: Pin definitions and descriptions.

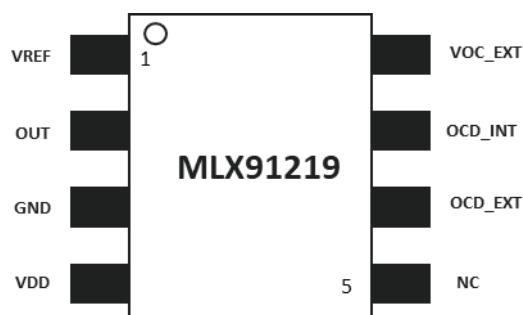


Figure 6: Pinout of SOIC8 package.

8. Absolute Maximum Ratings

Exceeding the absolute maximum ratings may cause permanent damage. Exposure to absolute maximum-rated conditions for extended periods of time may affect device reliability.

Parameter	Symbol	Value	Unit
Positive Supply Voltage (overvoltage)	V_{DD}	+8	V
Negative Supply Voltage	V_{DD}	-0.3	V
Positive Pin Voltage ²	V_{PIN}	$V_{DD} + 0.3$	V
Output Sink Current	I_{out_max}	50	mA
Output Source Current	I_{out_source}	25	mA
Output Short Circuit Current to GND	I_{SHORT_GND}	-100	mA
Output Short Circuit Current to V_{DD}	I_{SHORT_VDD}	60	mA
Reverse Pin Voltage ²	V_{min_REV}	GND-0.3	V
Maximum Junction Temperature	T_{j_MAX}	165	°C
Operating Ambient Temperature Range	T_A	-40 to +150	°C
Storage Temperature Range	T_S	-55 to +165	°C
Magnetic Flux Density	B_{MAX}	± 3	T
Human Body ESD Protection	ESD_{HBM}	2	kV
Charged Device Model ESD Protection	ESD_{CDM} All pins ESD_{CDM} Corner pins	500 750	V

Table 7: Absolute maximum ratings.

² Except for V_{DD} and GND

9. General Electrical Specifications

Operating Parameters $T_A = -40$ to 150°C , $V_{DD}=5$ V or 3.3 V.

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Nominal Supply Voltage	V_{DD}	MLX91219Lxx-Axx-5xx MLX91219Lxx-Axx-3xx	4.5 3.135	5 3.3	5.5 3.465	V
Positive Supply Voltage (maintaining application mode)	V_{DD}				6.5	V
Supply Current	I_{DD}	Without R_{LOAD} on output, in application mode $V_{DD}=5$ V $V_{DD}=3.3$ V		15.5 15	19 18	mA
V_{OUT} Output Resistance	R_{OUT}	$V_{OUT}=50\%V_{DD}$, $I_{LOAD}=10$ mA		1	5	Ω
Output Capacitive Load	C_{LOAD}	Output amplifier stability is optimized for this typical value	0	4.7	6	nF
Output Leakage current	I_{LEAK}	High impedance mode, $T_A=150^\circ\text{C}$		6	20	μA
Output Voltage Linear Swing	V_{OUT_LSW}	Pull-down or pull-up ≥ 10 k Ω $V_{DD} > 4.6$ V for Fixed Mode versions	10		90	% V_{DD}

Table 8: General electrical parameters.

10. Magnetic specification

Operating Parameters $T_A = -40$ to 150°C , $V_{DD}=5$ V or 3.3 V factory trimmed unless otherwise specified.

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Operational Magnetic Field Range	B_{OP}				± 400	mT
Linearity Error (Magnetic)	NL	B within B_{OP} , $T_A = 25^\circ\text{C}$			± 0.5	%FS
Programmable Sensitivity	S_{PROG}	Generic part	5		105	
		MLX91219LVA-AAA-500	6.5	7	22.5	
		MLX91219LVA-AAA-501	6.5	10	22.5	
		MLX91219LDC-ARA-501	6.5	10	22.5	
		MLX91219LVA-AAA-502	6.5	15	22.5	mV/mT
		MLX91219LVA-AAA-503	16	25	55	
		MLX91219LVA-ARA-503	16	25	55	
		MLX91219LVA-AAT-511	6.5	10	22.5	
Sensitivity accuracy (factory trimming)	S_{RES}	$B = B_{OP}$	-1		+1	%
Sensitivity Programming Resolution	S_{RES}	$B = B_{OP}$		0.5		%

Table 9: Magnetic specification.

11. Analog output specification

11.1. Definitions

11.1.1. Thermal Reference Drift

The thermal reference drift is the variation of the reference voltage (V_{REF}) over temperature. It is expressed in ppm/°C.

$$+ \Delta T_{VREF} = \left(\frac{V_{ref}[125^{\circ}C]}{V_{ref}[25^{\circ}C]} - 1 \right) \cdot \frac{1}{(125 - 25)} \cdot 10^6$$

$$- \Delta T_{VREF} = \left(\frac{V_{ref}[-40^{\circ}C]}{V_{ref}[25^{\circ}C]} - 1 \right) \cdot \frac{1}{(-40 - 25)} \cdot 10^6$$

11.1.2. Voltage Output Quiescent

V_{OQ} corresponds to the difference between the measured and the ideal outputs when no magnetic field is applied to the MLX91219 at $T_A=25^{\circ}C$.

$$V_{OQ} = V_{OUT}[0mT]_{measured} - V_{OUT}[0mT]_{ideal}$$

11.1.3. Thermal Offset Drift

ΔT_{VQ} corresponds to variation of V_{OQ} in temperature.

11.1.4. Sensitivity

The sensitivity is the ratio between the output of the MLX91219 and the input magnetic field.

For ratiometric devices, as the output will scale with the supply, sensitivity is expressed as [% V_{DD}]/mT. For simplicity, in the datasheet the sensitivity will be always expressed in mV/mT. For ratiometric devices, this corresponds to the sensitivity for $V_{DD}=5V$ or $3.3V$, depending on the settings of the sensor.

For fixed devices, the output does not vary with the V_{DD} , sensitivity is thus expressed as mV/mT.

11.1.5. Linearity Error

The linearity error is the deviation of the output from the expected linear behaviour. To obtain the linearity error, the magnetic field is swept from $-B_{FS}$ to B_{FS} , where B_{FS} is the full scale magnetic field. To decorrelate the thermal drift from the linearity error, the junction temperature should be fixed below $50^{\circ}C$.

$$NL = \frac{V_{out}[B] - BESTFIT(V_{out}[B])}{V_{out}[B_{FS}] - V_{out}[-B_{FS}]} \cdot 100 \text{ [%FS]}$$

11.1.6. Ratiometry Offset and Sensitivity Error

Ratiometric Mode

In Ratiometric mode, V_{OUT} and V_{REF} are scaled with the supply voltage. $V_{DDnom} = 5V$

Ratiometric V_{OQ} Error:

$$\Delta R_{V_{OQ}} = V_{OQ} [V_{DDnom}] - V_{OQ} [V_{DDnom} \pm 10\%] \cdot \frac{V_{DDnom}}{V_{DDnom} \pm 10\%} [mV]$$

Ratiometric Sensitivity Error:

$$\Delta R_S = 100 \cdot \left(1 - \frac{S[V_{DDnom} \pm 10\%]}{S[V_{DDnom}]} \cdot \frac{V_{DDnom}}{V_{DDnom} \pm 10\%} \right) [\%]$$

In the datasheet, the ratiometric error is expressed as $\frac{mV}{\%VDD}$ for the offset, and $\frac{\%S}{\%VDD}$ for the sensitivity. For instance, if the supply voltage changes by 3%, the typical error on the sensitivity will be $0.16 \frac{\%S}{\%VDD} \times 3\% = 0.48\%$.

Fixed Mode

In Fixed mode, V_{OUT} and V_{REF} are not scaled with the supply voltage. Ideally, they do not vary. $V_{DDnom} = 5V$

Non-Ratiometric V_{OQ} Error:

$$\Delta R_{V_{OQ}} = V_{OQ} [V_{DDnom} \pm 10\%] - V_{OQ} [V_{DDnom}] [mV]$$

Non-Ratiometric Sensitivity Error:

$$\Delta R_S = \left(\frac{S[V_{DDnom} \pm 10\%]}{S[V_{DDnom}]} - 1 \right) \cdot 100 [\%]$$

11.2. SIP-4 VA Accuracy specifications

Operating Parameters $T_A = -40$ to 150°C , $V_{DD}=5\text{ V}$ or 3.3 V factory trimmed unless otherwise specified.

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Voltage Output Quiescent	V_{OQ}	No magnetic field applied, $T_A=25^\circ\text{C}$	-5		5	mV
Ratiometric Offset Error ³	$\Delta^R V_{OQ}$	$V_{DD} = 5\text{V}$ $V_{DD} = 3.3\text{V}$		1.6 1		$\text{mV}/\%V_{DD}$
Thermal Offset Drift ⁴	$\Delta^T V_{OQ}$	$T_A = -40$ to 125°C $T_A = -40$ to 150°C ⁵	-5	± 5	5	mV
Total Offset drift ⁶	ΔV_{OQ}			± 6		mV
Ratiometric Sensitivity Error ³	$\Delta^R S$			0.16		$\%S/\%V_{DD}$
Thermal Sensitivity Drift ⁴	$\Delta^T S$	$T_A = -40^\circ\text{C}$ to 125°C $T_A = -40^\circ\text{C}$ to 150°C ⁵	-1	± 1	1	$\%S$
Total Sensitivity Drift ⁶	ΔS			± 1.5		$\%S$
Input referred noise spectral density	N_{SD}	within $\text{BW} = 1 \dots 400\text{kHz}$, Max Gain		210		nT/VHz

Table 10: Accuracy specifications – analog parameters.

The accuracy specifications are defined for the factory calibrated sensitivity. The achievable accuracy is dependent on the user's end-of-line calibration. Resolution for offset and offset drift calibration is better than $0.05\%V_{DD}$. Trimming capability is higher than measurement accuracy. End-user calibration can therefore increase the accuracy of the system.

³ Ratiometry Error is verified at maximum V_{DD} deviation ($5\%V_{DD}$ at 3.3V and $10\%V_{DD}$ at 5V) over temperature in production. Typical values are the maximum mean ± 3 sigma out of all characterized lots.

⁴ Performance after factory trimming.

⁵ Based on results from AEC-Q003 Characterization. Typical values are the maximum mean ± 3 sigma out of all characterized lots.

⁶ After 1000h HTOL at $T_A = 155^\circ\text{C}$ with respect to after pre-conditioning at $T_A = 35^\circ\text{C}$. Pre-conditioning is performed with MSL level 3 based on J-STD-020. Typical values are the highest average ± 3 sigma across all qualification lots.

11.3. SOIC8 Accuracy specifications

Operating Parameters $T_A = -40$ to 150°C , $V_{DD}=5$ V or 3.3 V factory trimmed unless otherwise specified.

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Voltage Reference	V_{REF}	$T_A=25^\circ\text{C}$, AFx-5xx versions, RS=0	2.48	2.5	2.52	V
		$T_A=25^\circ\text{C}$, AFx-3xx versions, RS=1	1.64	1.65	1.66	
		$T_A=25^\circ\text{C}$, AFx-3xx versions, RS=2	1.492	1.5	1.508	
		$T_A=25^\circ\text{C}$, AFx-2xx/AFx-4xx, RS=3	0.495	0.5	0.505	
Thermal Reference Drift	ΔV_{REF}	Variation versus 25°C , for fixed output			± 150	ppm/ $^\circ\text{C}$
Non-ratiometric VREF Error	ΔV_{REF}	Fixed mode devices (only SOIC8)	-3		3	mV
Voltage Output Quiescent	V_{OQ}	No magnetic field applied, $T_A=25^\circ\text{C}$	-5		5	mV
Ratiometric Offset Error ⁷	$\Delta^R V_{OQ}$	$V_{DD} = 5\text{V}$ $V_{DD} = 3.3\text{V}$		1.6 1		mV/% V_{DD}
Non-Ratiometric Offset Error	$\Delta^R V_{OQ}$	$V_{DD} = 5\text{V}$ $V_{DD} = 3.3\text{V}$		5 5		mV
Thermal Offset Drift ⁸	$\Delta^T V_{OQ}$	$T_A = -40$ to 125°C $T_A = -40$ to 150°C ⁹	-5	± 6	5	mV
Total Offset drift ¹⁰	ΔV_{OQ}			± 6		mV
Ratiometric Sensitivity Error ⁷	$\Delta^R S$			0.16		%S/% V_{DD}
Non-Ratiometric Sensitivity Error	$\Delta^R S$		-0.6		0.6	%S
Thermal Sensitivity Drift ⁸	$\Delta^T S$	$T_A = -40^\circ\text{C}$ to 125°C $T_A = -40^\circ\text{C}$ to 150°C ⁹	-1.5	± 1.3	1.5	%S
Total Sensitivity Drift ¹⁰	ΔS			± 1.5		%S
Input referred noise spectral density	N_{SD}	within BW = 1 .. 400kHz, Max Gain		210		nT/VHz

Table 11: Accuracy specifications – analog parameters.

The accuracy specifications are defined for the factory calibrated sensitivity. The achievable accuracy is dependent on the user's end-of-line calibration. Resolution for offset and offset drift calibration is better than 0.05% V_{DD} . Trimming capability is higher than measurement accuracy. End-user calibration can therefore increase the accuracy of the system.

⁷ Ratiometry Error is verified at maximum V_{DD} deviation (5% V_{DD} at 3.3V and 10% V_{DD} at 5V) over temperature in production. Typical values are the maximum mean ± 3 sigma out of all characterized lots.

⁸ Performance after factory trimming.

⁹ Based on results from AEC-Q003 Characterization. Typical values are the maximum mean ± 3 sigma out of all characterized lots.

¹⁰ After 1000h HTOL at $T_A = 155^\circ\text{C}$ with respect to after pre-conditioning at $T_A = 35^\circ\text{C}$. Pre-conditioning is performed with MSL level 3 based on J-STD-020. Typical values are the highest average ± 3 sigma across all qualification lots.

11.4. Timing specifications

Operating Parameters $T_A = -40$ to 150°C , $V_{DD}=5$ V or 3.3 V factory trimmed unless otherwise specified.

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Step Response Time	T_{RESP}	Delay between the input signal reaching 90% and the output reaching 90% (see Figure 7) SF=1 (default) SF=2 SF=3		2		μs
Bandwidth	BW	-3dB, $TA = 25^\circ\text{C}$, SF=1 (default) SF=2 SF=3	400			
			200			
			100			
Power on Delay ¹¹	T_{POD}			1		ms

Table 12: Timing specifications of the high-speed analog output

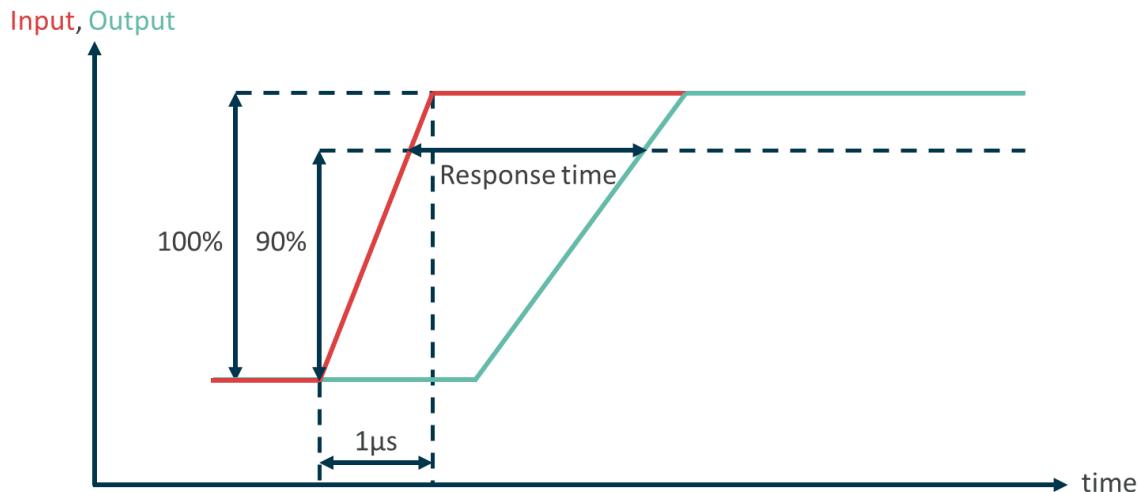


Figure 7: Response Time definition

¹¹During the power on, the output follows a routine and is not valid (i.e. it is not related to magnetic field) for $T_{POD}=1\text{ms}$.

12. Diagnostics

It is possible to take advantage of diagnostic features, with the help of adding a pull-down resistor (see Section 14). If a failure event occurs, the measured output will be set to ground. This can be interpreted as failure by the microcontroller unit.

Error	Effect on Output
Calibration data CRC Error	Output stage in high-Z mode. A pull-down resistor to ground will result in output equal to ground.
VDD Under voltage Thresholds:	Output is pulled to GND with a $2\text{k}\Omega$ resistance, until VDD is inside the specified ranges, depending if the device is powering on or off. <ul style="list-style-type: none"> Power-up: $\text{VDD} < 2.8\text{V}$ Power-down: $\text{VDD} < 2.5\text{V}$
Broken OUT	Pull-down external resistor allows to measure a voltage equal to GND.

Table 13: Description of the diagnostic modes in MLX91219

13. Overcurrent Detection Specification

13.1. General

The MLX91219 provides two OCD features (called internal and external) that allow the detection of overcurrent events. The internal OCD (OCD_{INT}) is available in both packages SIP4-VA and SOIC8, while the external OCD (OCD_{EXT}) is only available in SOIC8 package. When an overcurrent event occurs, the OCD pins are pulled to ground. During normal operation the OCD voltage remains at V_{DD} . If not used, OCD pins can be connected to GND.

The two OCD functions are able to react to an overcurrent event within few μs of response time. To avoid false alarm, the overcurrent has to be maintained for at least $1\mu\text{s}$ for the detection to occur. After detection by the sensor the output flag is maintained for $10\mu\text{s}$ of dwell time. This allows the overcurrent to be easily detected at microcontroller level. Table 14 offers a comparison between OCD_{INT} and OCD_{EXT} :

Description	OCD_{INT}	OCD_{EXT}
Typical Application	Short-circuit detection	Out-of-range detection
Overcurrent effect	OCD_{INT} pin to GND	OCD_{EXT} pin to GND
Detection mode	Bidirectional	Unidirectional / bidirectional
Threshold trimming	EEPROM	Voltage divider on VOC_{EXT}
Availability in package	SIP4-VA, SOIC8	SOIC8

Table 14: Comparison between OCD_{INT} and OCD_{EXT}

13.2. Electrical Specifications

Operating Parameters $T_A = -40$ to 150°C , $V_{DD}=5$ V or 3.3 V factory trimmed unless otherwise specified.

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
OCD _{INT} Internal ON Resistance	$R_{ON_OCD_INT}$	$I_{SINK} = 1$ mA	60	90	150	Ω
OCD _{EXT} Internal ON Resistance	$R_{ON_OCD_EXT}$	$I_{SINK} = 1$ mA	160	190	280	Ω
VOC _{EXT} Voltage Range ¹² $V_{DD}=5$ V, 5xx versions	VOC _{EXT_5V}	RS = 0, Bidirectional RS = 3, Unidirectional	0.5 0.9		2.0 4.5	V
VOC _{EXT} Voltage Range ¹² $V_{DD}=3.3$ V, 3xx versions	VOC _{EXT3V3}	RS = 1, Bidirectional RS = 3, Unidirectional	0.5 0.74		1.525 2.9	V
OCD _{INT} accuracy	OCD _{INT}	Ratiometric output ¹³		± 10		%Thr ¹⁴
OCD _{EXT} accuracy	OCD _{EXT}			± 1.5		%FS

Table 15: Electrical Specifications OCD

13.3. Timing Specifications

Operating Parameters $T_A = -40$ to 150°C , $V_{DD}=5$ V or 3.3 V factory trimmed unless otherwise specified.

Parameter	Test Conditions	Min	Typ	Max	Units
OCD _{INT} response time	programmable		1.4 2.1		μs
OCD _{EXT} response time			10		μs
OCD _{INT} required Input holding time			0.5		μs
OCD _{EXT} required Input holding time			10		μs
OCD _{INT} output dwell time		7		14	μs
OCD _{EXT} output dwell time			10		μs

Table 16: OCD_{INT} and OCD_{EXT} timing specifications

¹² VOC_{EXT} defines the OCD_{EXT} threshold. In case of a ratiometric device, VOC_{EXT} should change with Vdd to avoid additional errors.

¹³ OCD_{INT} threshold will not scale with VDD variation (in ratiometric output mode) therefore at lower supply voltage results in a higher OCD_{INT} threshold and vice versa. VDD variation should be accounted for when defining the OCD threshold.

¹⁴ The error of OCD_{INT} is expressed as percentage of the threshold value. Example: if the nominal threshold is 282mT, the typical threshold of OCD_{INT} will be in the range between 253.8mT and 310.2

13.4. Internal Overcurrent Detection Principle

The internal OCD takes the threshold voltage values predefined in the EEPROM and does not require any extra components. The OCD_{INT} implementation allows detecting overcurrent outside of the output measurement range of the sensor and is therefore suitable for large current peaks as occurring during short-circuit. If the theoretical sensor output overcomes the OCD_{INT} voltage threshold, the overcurrent event is flagged on OCD_{INT} pin. The default OCD threshold voltages are defined as follows, but other values can be set on request.

Sensor reference	Typical Sensitivity [mV/mT]	OCD_{INT} Threshold Current [%FS]
MLX91219LVA-AAA-500	7	134.7
MLX91219LVA-AAA-501	10	134.7
MLX91219LDC-ARA-501	10	134.7
MLX91219LVA-AAA-502	15	134.7
MLX91219LVA-AAA-503	25	134.7
MLX91219LDC-ARA-503	25	134.7
MLX91219LVA-AAT-511	10	88.2

Table 17: OCD_{INT} thresholds

	Sensor configuration	Min [% FS]	Max [% FS]
OCD_{INT} Threshold	$V_{DD} = 5V / V_{REF} = 2.5V$	25.5	215.8

Table 18: OCD_{INT} factory programmable range

13.5. External Overcurrent Detection Principle

The external OCD uses the voltage applied on VOC_{EXT} pin as threshold voltage. This translates into an overcurrent threshold depending on the sensitivity of the sensor. A voltage divider on VOC_{EXT} allows defining the threshold voltage in a custom way. Depending on the voltage divider configuration, the OCD_{EXT} can be used either in bidirectional or unidirectional mode. The External OCD threshold is defined within the measurement range of the sensor output. This feature is then suitable for out-of-range detection where the OCD threshold remains close to the nominal current. It offers a better accuracy than OCD_{INT} but the response is slower. The below table presents the unidirectional and bidirectional external OCD configurations. Please refer to section 14 for more details about the application diagram and the recommended resistances.

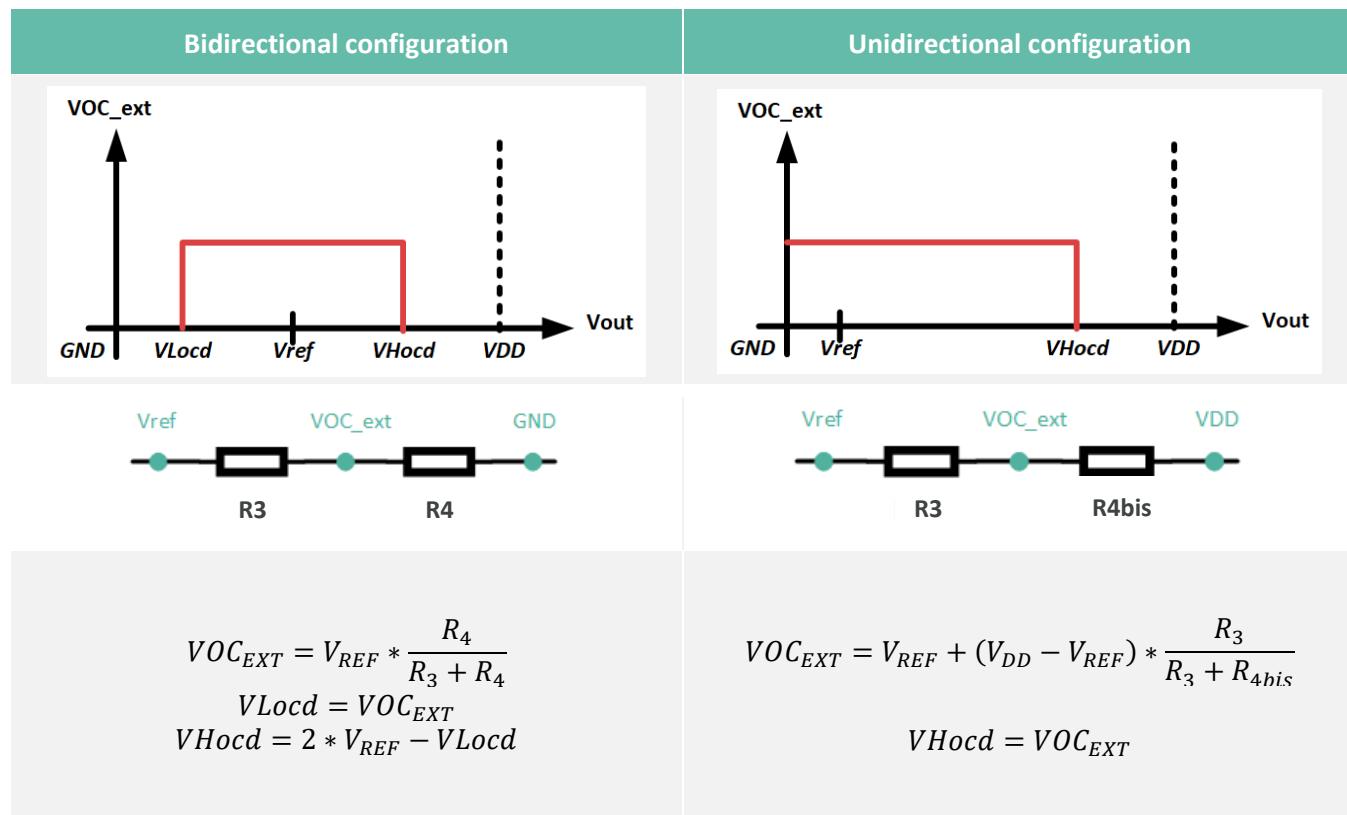


Table 19: External OCD, bidirectional and unidirectional configurations

14. Recommended Application Diagram

14.1. SIP-4 VA Package

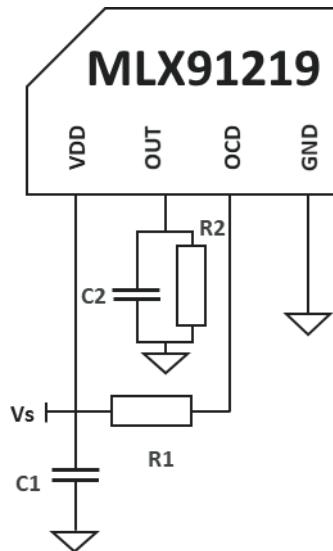
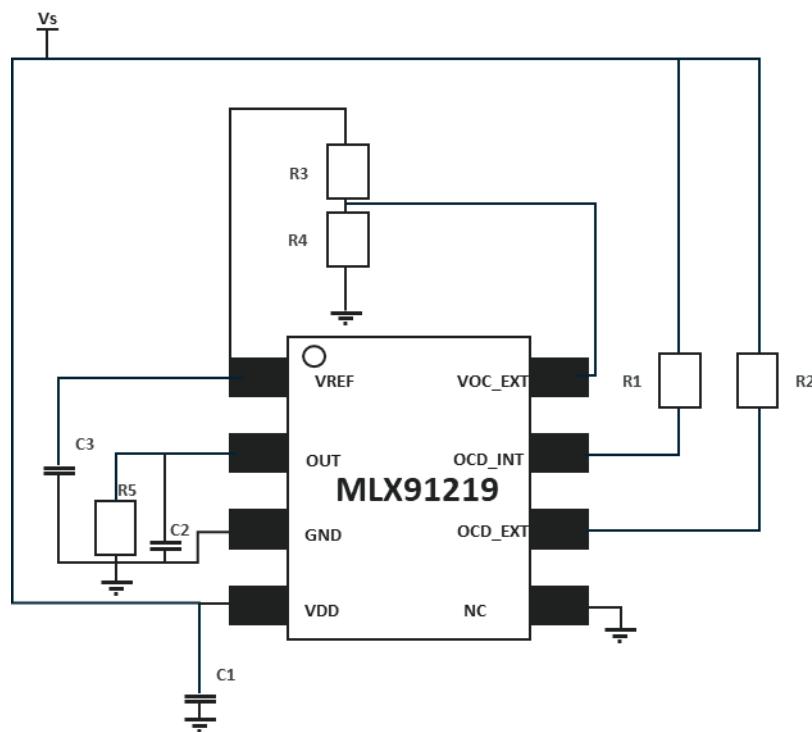


Figure 8: Application Diagram for SIP-4 VA package

Part	Description	Value	Unit
C1	Supply capacitor, EMI, ESD	47	nF
C2	Decoupling, EMI, ESD	4.7	nF
R1	Internal OCD resistor	10	kΩ
R2	Output pull-down resistor	>10	kΩ

Table 20: Resistor and capacitor values for SIP-4 VA package

14.2. SOIC8 package

Figure 9: Application Diagram for SOIC8 package, bidirectional OCD_{EXT}.

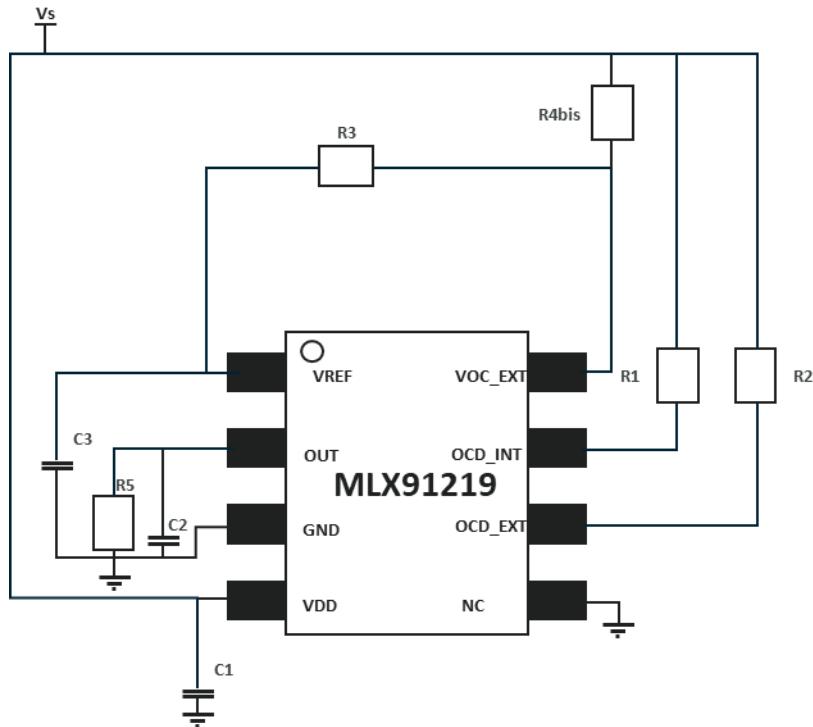


Figure 10: Application Diagram for SOIC8 package, unidirectional OCD_{EXT}.

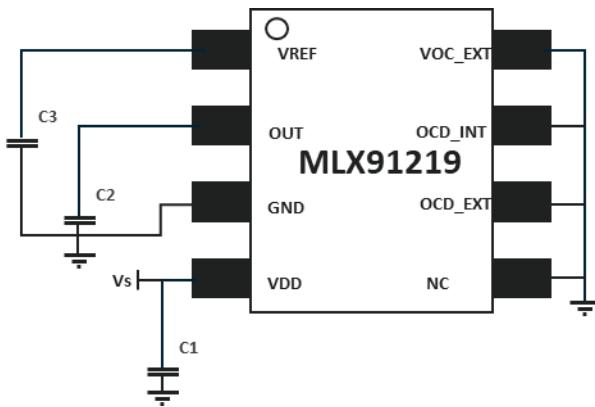


Figure 11: Application Diagram for SOIC8 package, bidirectional OCD_{EXT}.

Part	Description	Value	Unit
C1	Supply capacitor, EMI, ESD	47	nF
C2	Decoupling, EMI, ESD	4.7	nF
C3	Decoupling, EMI, ESD	47	nF
R1	Internal OCD resistor	10	kΩ
R2	External OCD resistor	10	kΩ
R ₃ + R ₄ / R _{4_BIS}	External OCD Resistor	>200	kΩ
R ₄ or R _{4_BIS}	External OCD Resistor	custom	-
R5	Output pull-down resistor	>10	kΩ

Table 21: Resistor and capacitor values for SOIC8 package

14.3. Resistance on reference voltage pin

The resistance connected to the reference pin should be large enough to limit the current. Figure 12 shows an example of the case when the resistance on the reference pin is too low. The measured V_{REF} will be equal to $V_{REF} = V_{REF_INT} \times \frac{R_{EXT}}{R_{EXT} + R_{REF}} = 1.25V$. Therefore, the current I_{REF} will be equal to $I_{REF} = \frac{V_{REF}}{R_{EXT}} = 6.25mA$.

The maximum source current on the reference pin is 0.6mA (typical value). Therefore, the current flowing will be 0.6mA, and the measured V_{REF} will be $V_{REF} = 0.6mA \times 200\Omega = 0.12V$. To conclude, to measure the correct reference voltage, it is important to have the resistance on the reference pin larger than the internal resistance, normally larger than 200kΩ.

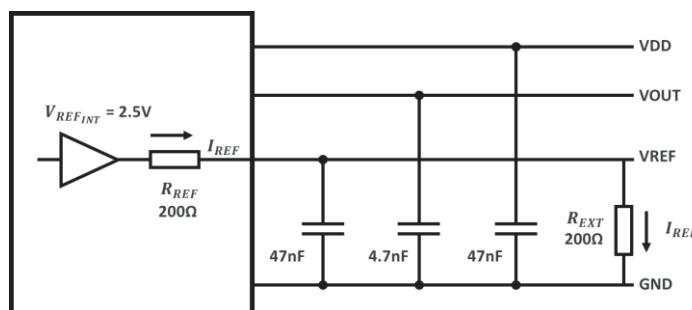


Figure 12: Case when the external resistance on reference pin is low.

15. Standard Information

Our products are classified and qualified regarding soldering technology, solderability and moisture sensitivity level according to standards in place in Semiconductor industry.

Soldering of SMDs (Surface Mount Devices)

For Surface Mounted Devices (SMD, as defined according to JEDEC norms), the only applicable soldering method is reflow. For more information, read the application note **Soldering for Surface Mount Technology (SMT)** at the link <https://media.melexis.com/-/media/files/documents/application-notes/handling-and-assembly/guidelines-surface-mount-technology-smt-soldering-application-note-melexis.pdf>.

Lead pre-forming of THDs (Surface Mount Devices)

THD lead pre-forming (cutting and/or bending) is applicable under strict compliance with Melexis Guidelines for lead forming of SIP Hall Sensors. For more information, read the application note **Lead forming of Hall sensors in SIP packages** at the link <https://www.melexis.com/en/tech-info/ic-handling-and-assembly/lead-forming>.

Soldering of THDs (Surface Mount Devices)

For Through Hole Devices (THD), the applicable soldering methods are reflow, wave, selective wave and robot point-to-point. For more information, read the application note **Soldering of Through Hole Devices (THD)** at the link <https://media.melexis.com/-/media/files/documents/application-notes/handling-and-assembly/guidelines-through-hole-device-thd-soldering-application-note-melexis.pdf?ts=20211210t1158483507>.

Soldering on PCB

Melexis products soldering on PCB should be conducted according to the requirements of IPC/JEDEC and J-STD-001. Solder quality acceptance should follow the requirements of IPC-A-610.

Environmental information

Melexis is contributing to global environmental conservation by promoting **lead free** solutions. For more information on qualifications of **RoHS** compliant products (RoHS = European directive on the Restriction Of the use of certain Hazardous Substances) please visit the quality page on our website (<https://www.melexis.com/en/quality-environment>).

16. ESD Precautions

Electronic semiconductor products are sensitive to Electro Static Discharge (ESD). Always observe Electro Static Discharge control procedures whenever handling semiconductor products.

17. Packaging information: SIP4-VA

17.1. Sensor active measurement direction and magnetic center

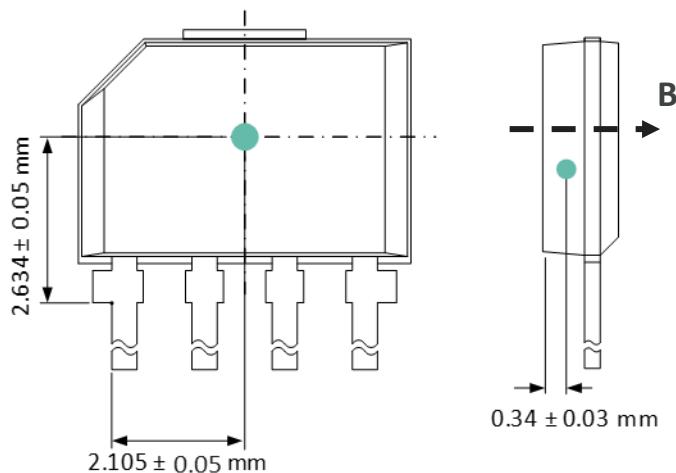


Figure 13: VA/SIL-4L Magnetic center and sensor's active measurement direction B

17.2. Package marking & Hall plate position

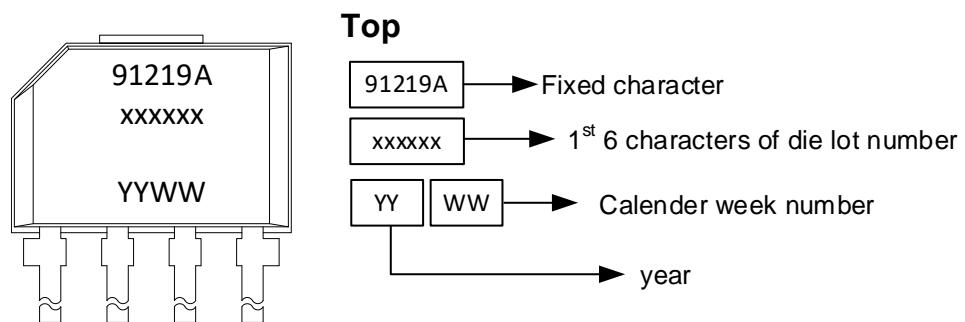


Figure 14. VA/SIP 4L (single in-line package) / 18mm lead length - Package Information

17.3. VA Straight leg (MLX91219LVA-AAA-xxx-xx)

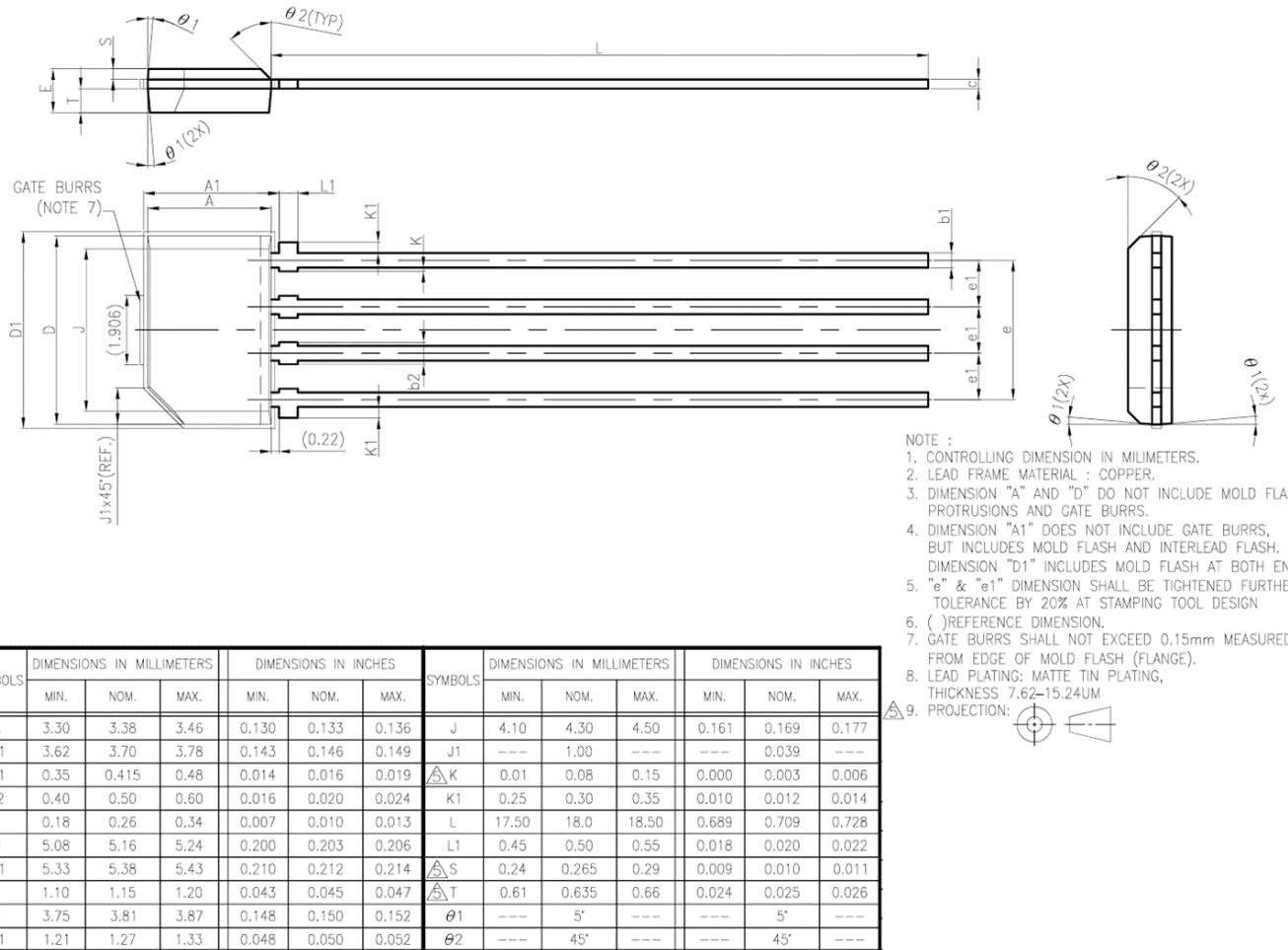


Figure 15: VA Straight leg

17.4. Trim and Form type: 90° 2x2x91.3 (h=5.34mm) Bending-STD2 (MLX91219LVA-AAR-xxx-xx)

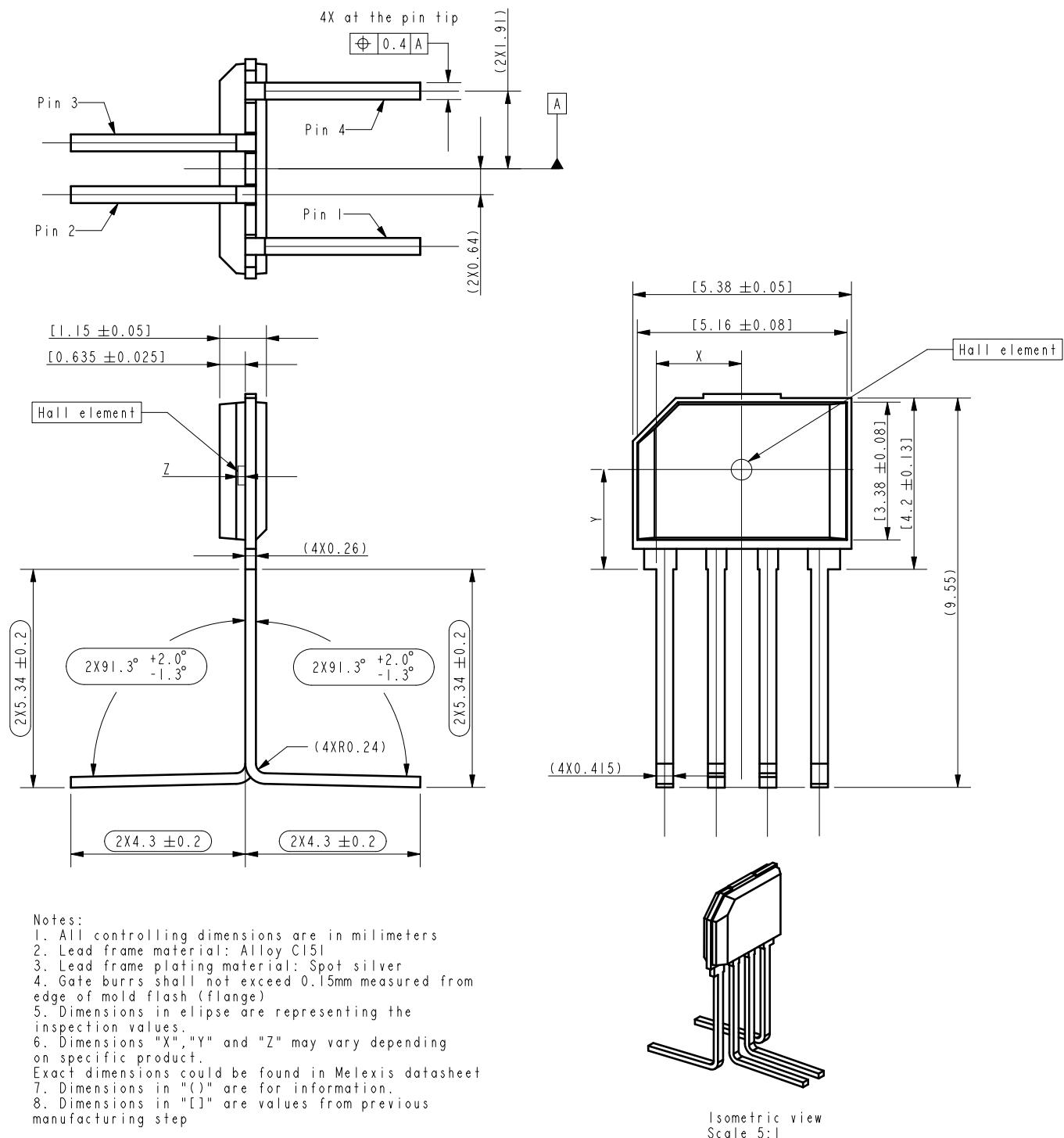
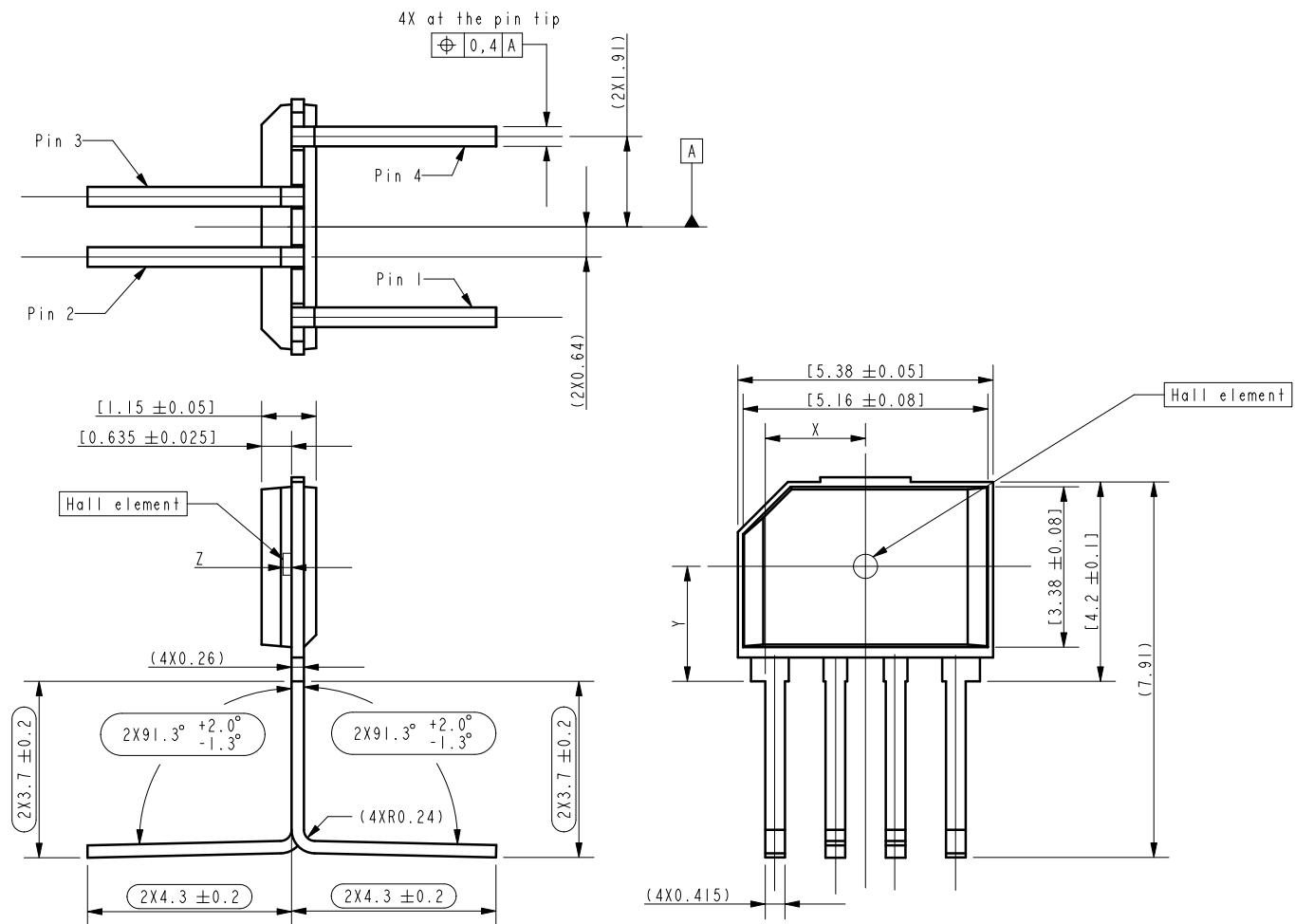


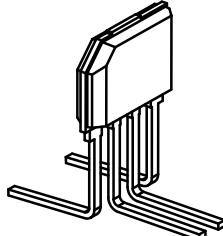
Figure 16: Trim and form type: 90° 2x2x91.3 (h=5.34), bending-STD2 (AAR-xxx)

17.5. Trim and Form type: 90° 2x2x91.3 (h=3.7mm) Bending-STD3 (MLX91219LVA-AAS-xxx-xx)



Notes:

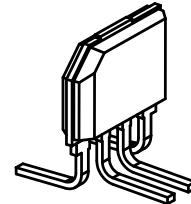
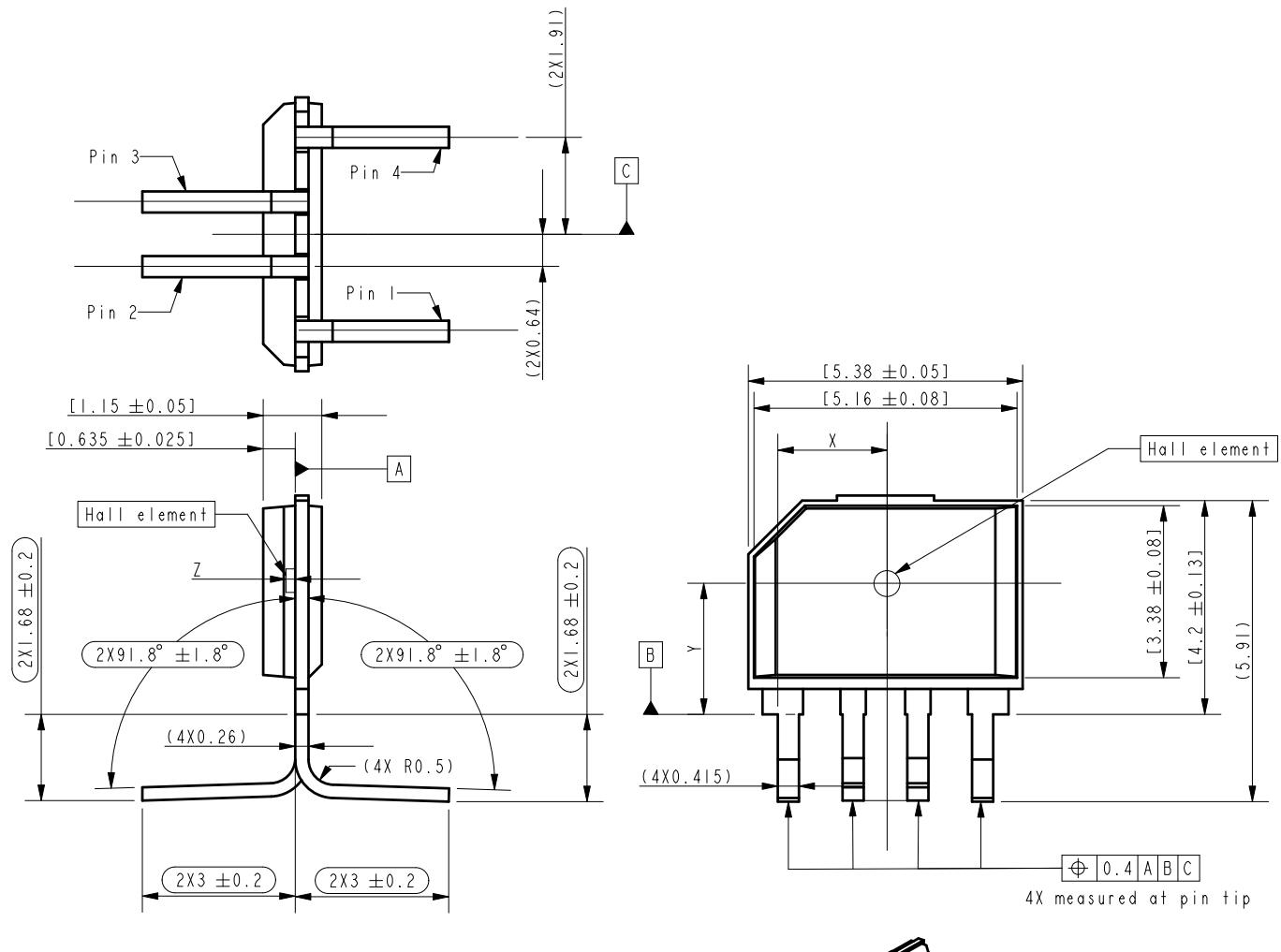
1. All controlling dimensions are in millimeters
2. Lead frame material: Alloy C151
3. Lead frame plating material: Spot silver
4. Gate burrs shall not exceed 0.15mm measured from edge of mold flash (flange)
5. Dimensions in ellipse are representing the inspection values.
6. Dimensions "X", "Y" and "Z" may vary depending on specific product.
- Exact dimensions could be found in Melexis datasheet
7. Dimensions in "(" are for information.
8. Dimensions in "[]" are values from previous manufacturing step



Isometric view
Scale 5:1

Figure 17: Trim and form type: 90° 2x2x91.3 (h=3.7), bending-STD3 (AAS-xxx)

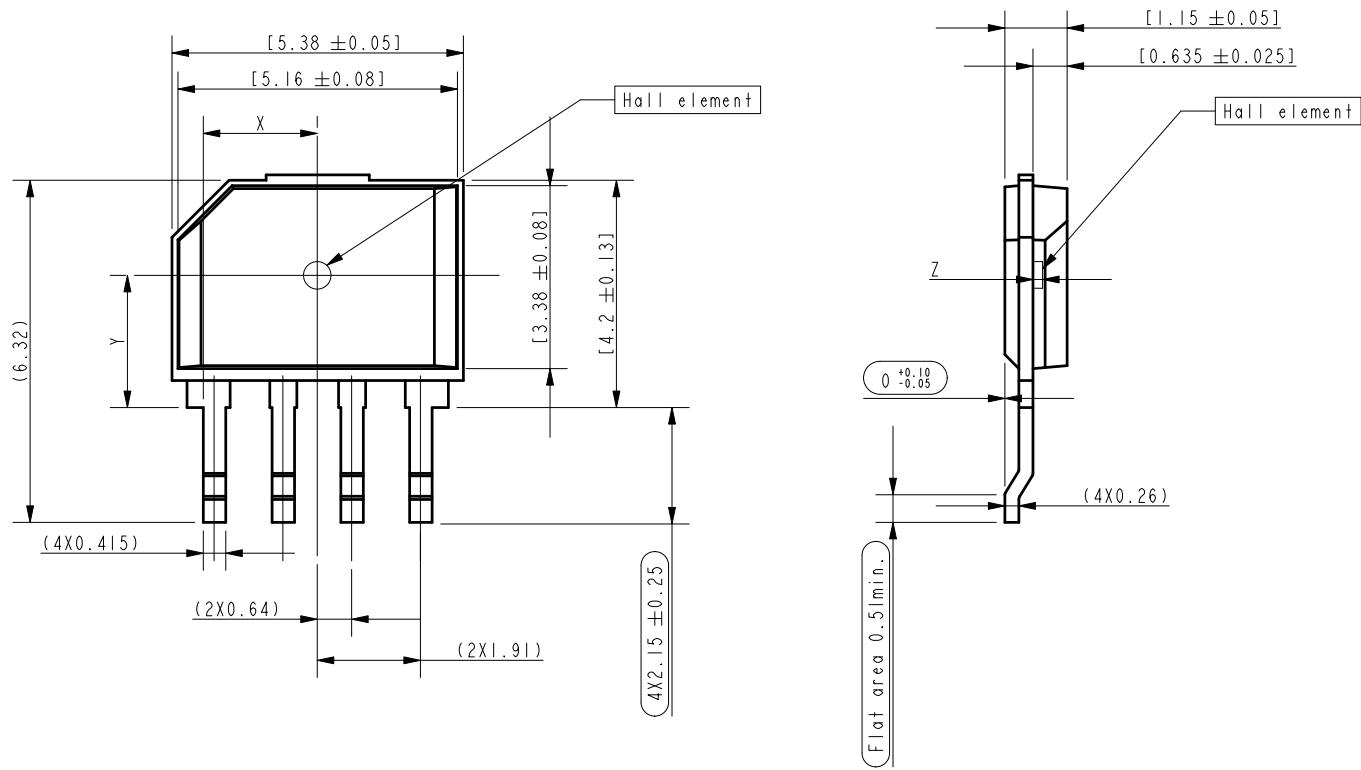
17.6. Trim and Form type: 90° 2x2x91.8 (h=1.68mm) Bending-STD4 (MLX91219LVA-AAT-xxx-xx)



Isometric view
Scale 5:1

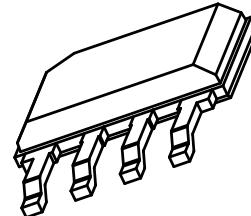
Figure 18: Trim and form type: 90° 2x2x91.8 (h=1.68), bending-STD4 (AAT-xxx)

17.7. Trim and Form type: SMD style TFT4K1 (MLX91219LVA-AAZ-xxx-xx)



Notes:

1. All controlling dimensions are in millimeters
2. Lead frame material: Alloy C151
3. Lead frame plating material: Spot silver
4. Gate burrs shall not exceed 0.15mm measured from edge of mold flash (flange)
5. Dimensions in ellipse are representing the inspection values.
6. Dimensions "X", "Y" and "Z" may vary depending on specific product.
- Exact dimensions could be found in Melexis datasheet
7. Dimensions in "()" are for information.
8. Dimensions in "[]" are values from previous manufacturing step



Isometric view
Scale 5:1

Figure 19: Trim and form SMD style TFT4K1 (AAZ-xxx)

18. Packaging information: SOIC8

18.1. Sensor active measurement direction and magnetic center

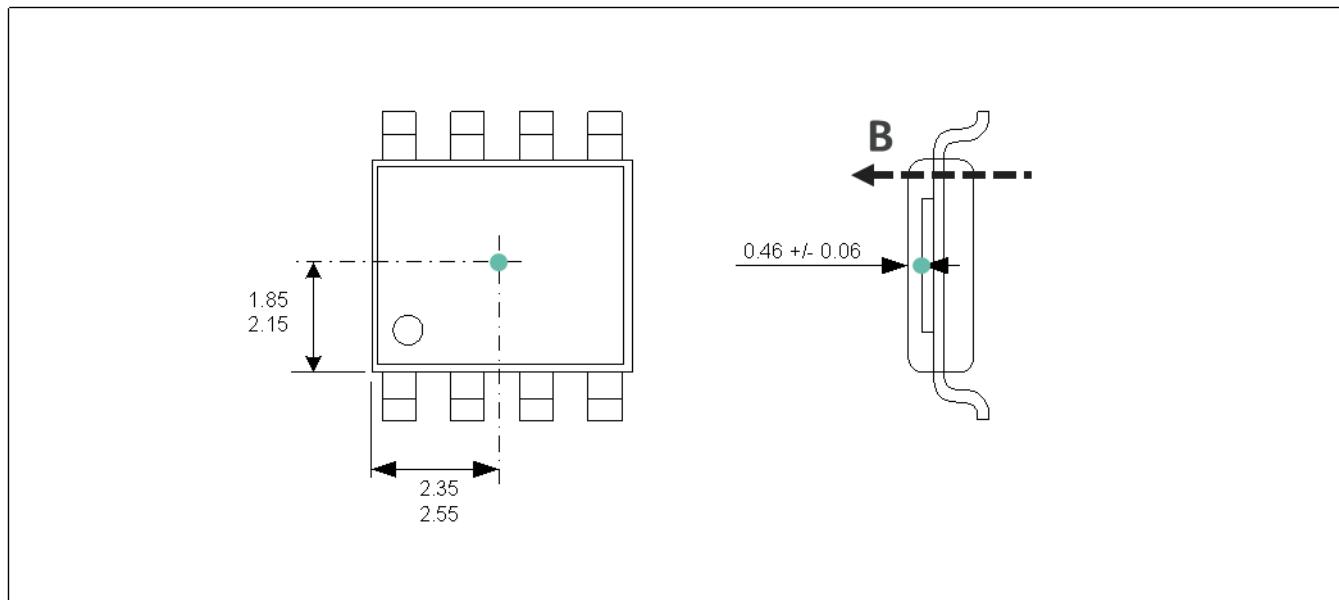


Figure 20: VA/SIL-4L Magnetic center and sensor's active measurement direction B

18.2. Package marking

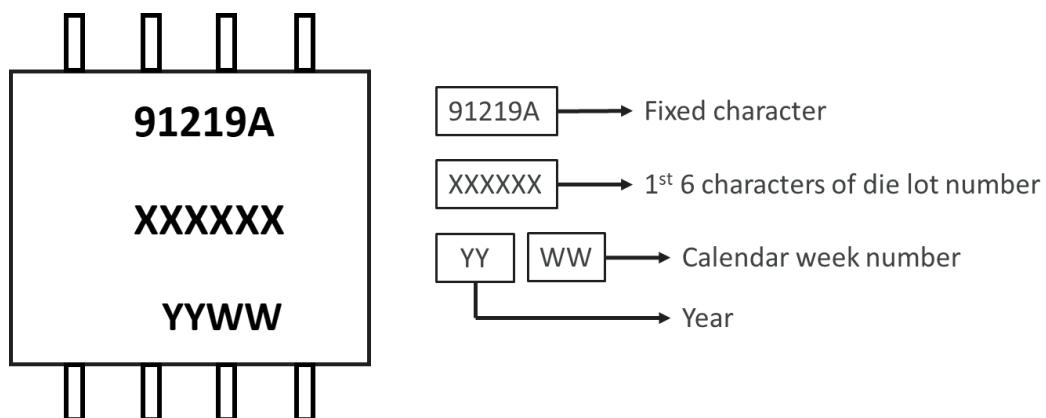


Figure 21. SOIC8 package marking

18.3. Package dimensions

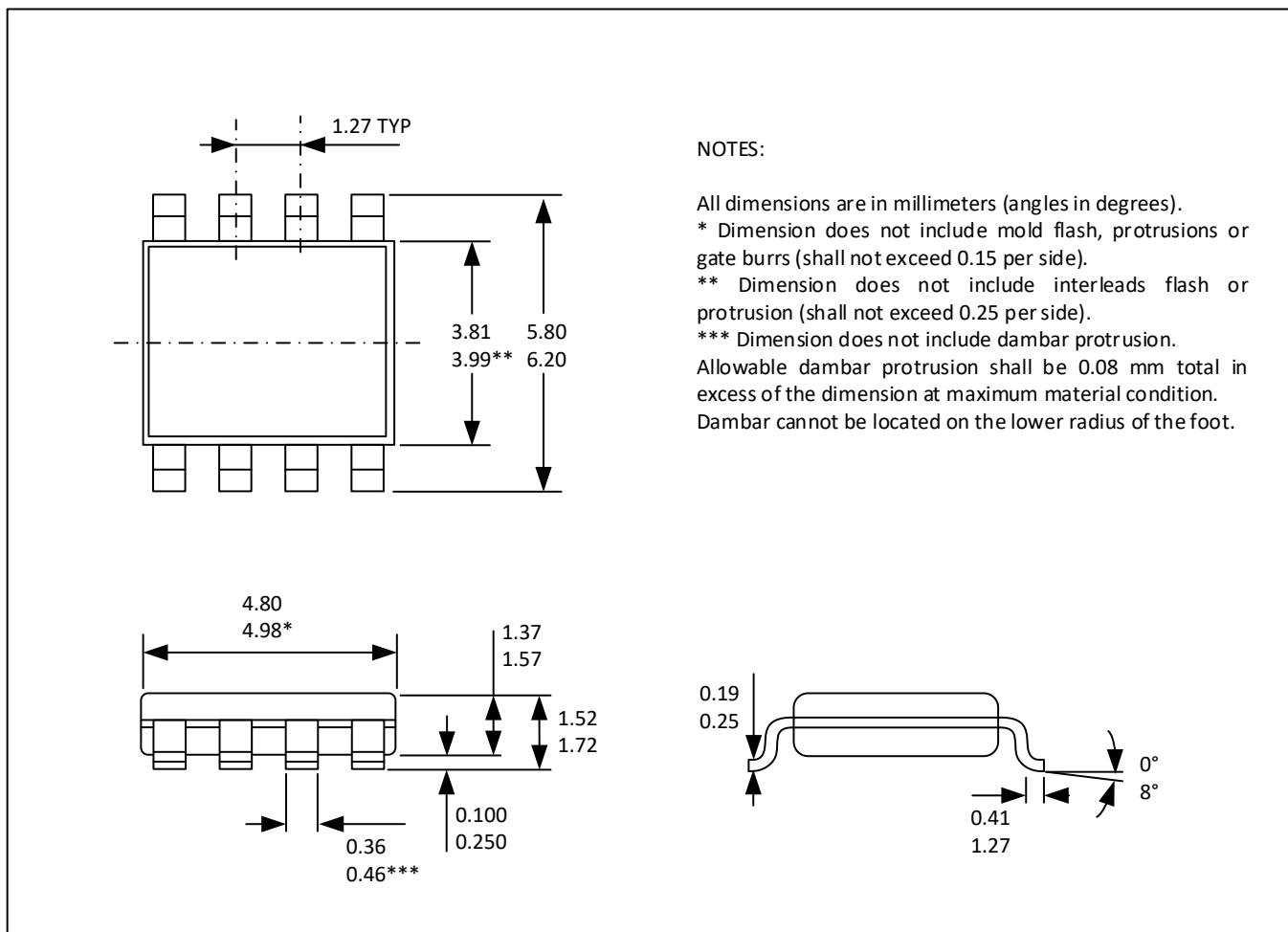


Figure 22: SOIC8 package

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